

Monocrystalline silicon wafer specification

Length of wafer edge	6inch: 125±0.5mm 6.5inch:125±0.5mm 8inch: 156±0.5mm
Diagonal	6inch: 150±0.5mm 6.5inch:165±0.5mm 8inch: 200±0.5mm
Conductivity type	P-type
Dopant	Boron
Thickness	200±20μm
Resistivity	1-3Ωcm 3-6Ωcm
Oxygen concentration	<1X10 ¹⁸ atoms/cm ³
Carbon concentration	<5X10 ¹⁶ atoms/cm ³
Lifetime	≧ 10μs
Chamfer discrepancy	0.5mm
Vertical angle deviate	90±0.3°
Orientation	<100>±2°
Dislocation Density	≧ 3000/cm ²
TTV	<uniwafer thickness 15% <30μm
Warp	<50μm
Saw marks	<15μm
Cracks and pin holes	No visual cracks and V-type pin holes
Edge	No edge defect and silicon drop
Surface	1.As clean,cut,No stains and detergent vestigital. 2.No visual knife marks,concave pit.